

General Description

Renesas SLG7RN46453 is a low power and small form device. The SoC is housed in a 1mm x 1.2mm STQFN package which is optimal for using with small devices.

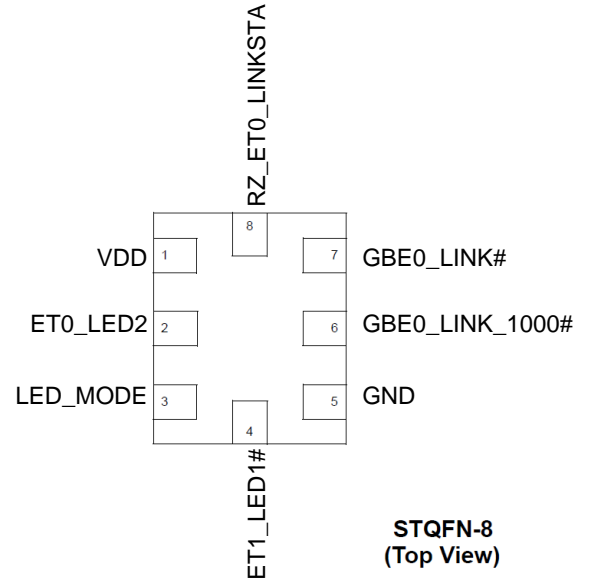
Features

- Low Power Consumption
- Pb - Free / RoHS Compliant
- Halogen - Free
- STQFN - 8 Package

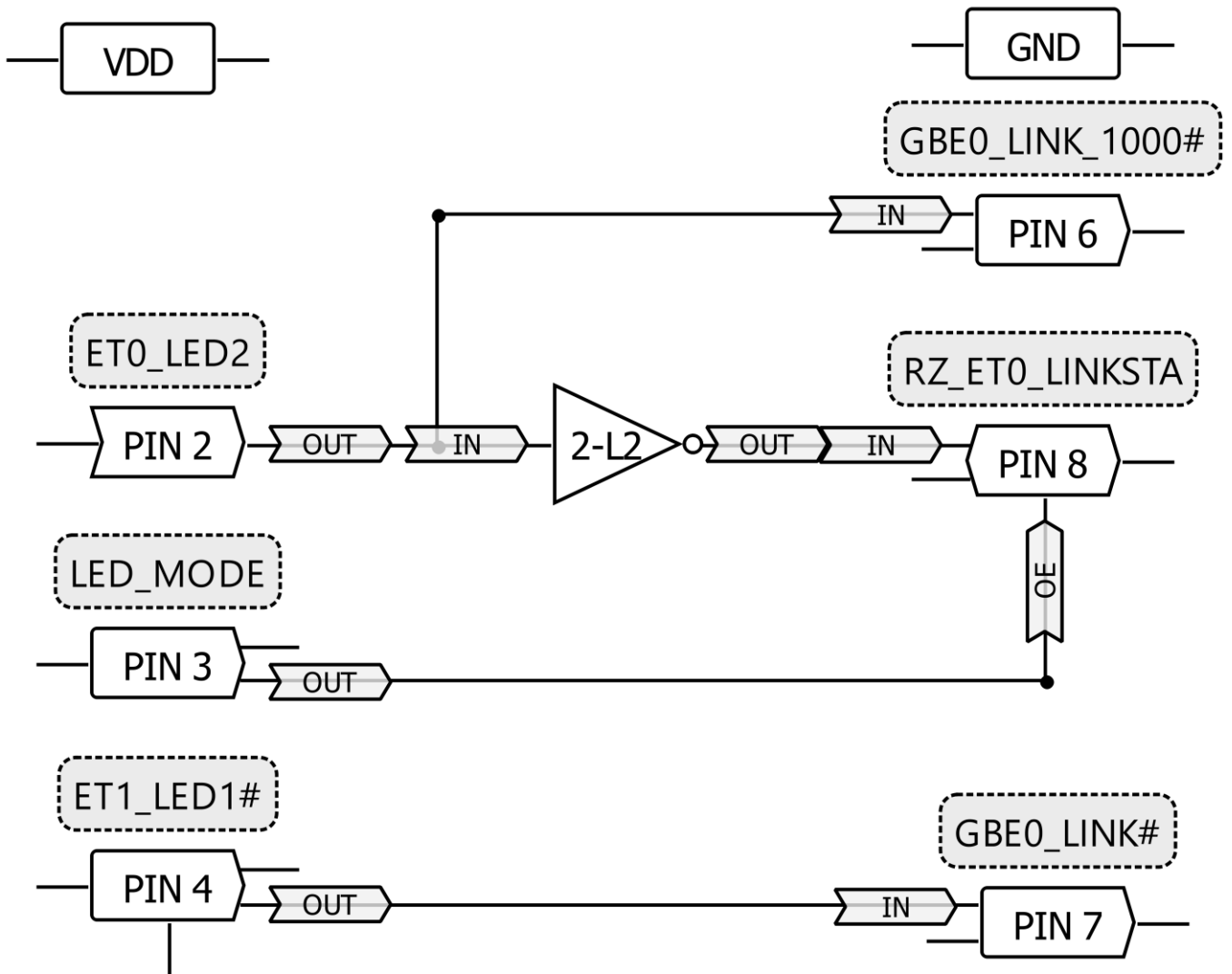
Output Summary

2 Outputs - Open Drain NMOS 2X
 1 Output - Push Pull 1X

Pin Configuration



Block Diagram



Pin Configuration

Pin #	Pin Name	Type	Pin Description	Internal Resistor
1	VDD	PWR	Supply Voltage	--
2	ET0_LED2	Digital Input	Low Voltage Digital Input	floating
3	LED_MODE	Digital Input	Low Voltage Digital Input	floating
4	ET1_LED1#	Digital Input	Low Voltage Digital Input	floating
5	GND	GND	Ground	--
6	GBE0_LINK_1000#	Digital Output	Open Drain NMOS 2X	floating
7	GBE0_LINK#	Digital Output	Open Drain NMOS 2X	floating
8	RZ_ET0_LINKSTA	Bi-directional	Digital Input without Schmitt trigger / Push Pull 1X	floating

Ordering Information

Part Number	Package Type
SLG7RN46453V	8-pin STQFN
SLG7RN46453V	8-pin STQFN - Tape and Reel (3k units)

Absolute Maximum Conditions

Parameter	Min.	Max.	Unit
Supply Voltage on VDD relative to GND	-0.5	7	V
DC Input Voltage	GND - 0.5V	VDD + 0.5V	V
Maximum Average or DC Current (Through pin)	Push-Pull 1x	8	mA
	OD 2x	12	
Current at Input Pin	-1.0	1.0	mA
Input leakage (Absolute Value)	--	1000	nA
Storage Temperature Range	-65	150	°C
Junction Temperature	--	150	°C
ESD Protection (Human Body Model)	2000	--	V
ESD Protection (Charged Device Model)	1300	--	V
Moisture Sensitivity Level	1		

Electrical Characteristics

Symbol	Parameter	Condition/Note	Min.	Typ.	Max.	Unit
V _{DD}	Supply Voltage		1.71	3.3	5.5	V
T _A	Operating Temperature		-40	25	85	°C
C _{VDD}	Capacitor Value at VDD		--	0.1	--	μF
C _{IN}	Input Capacitance		--	4	--	pF
I _Q	Quiescent Current	Static inputs and floating outputs	--	1	--	μA
V _O	Maximal Voltage Applied to any PIN in High-Impedance State		--	--	VDD	V
I _{VDD}	Maximum Average or DC Current Through VDD Pin (Per chip side, see Note 2)	T _J = 85°C	--	--	45	mA
		T _J = 110°C	--	--	22	mA
I _{GND}	Maximum Average or DC Current Through GND Pin (Per chip side, see Note 2)	T _J = 85°C	--	--	84	mA
		T _J = 110°C	--	--	40	mA
V _{IH}	HIGH-Level Input Voltage	Logic Input at VDD=1.8V	1.071	--	VDD	V
		Logic Input at VDD=3.3V	1.84	--	VDD	V
		Logic Input at VDD=5.0V	2.744	--	VDD	V
		Low-Level Logic Input at VDD=1.8V	0.936	--	VDD	V
		Low-Level Logic Input at VDD=3.3V	1.086	--	VDD	V
		Low-Level Logic Input at VDD=5.0V	1.185	--	VDD	V
V _{IL}	LOW-Level Input Voltage	Logic Input at VDD=1.8V	0	--	0.73	V
		Logic Input at VDD=3.3V	0	--	1.255	V
		Logic Input at VDD=5.0V	0	--	1.877	V
		Low-Level Logic Input at VDD=1.8V	0	--	0.517	V
		Low-Level Logic Input at VDD=3.3V	0	--	0.669	V
		Low-Level Logic Input at VDD=5.0V	0	--	0.765	V

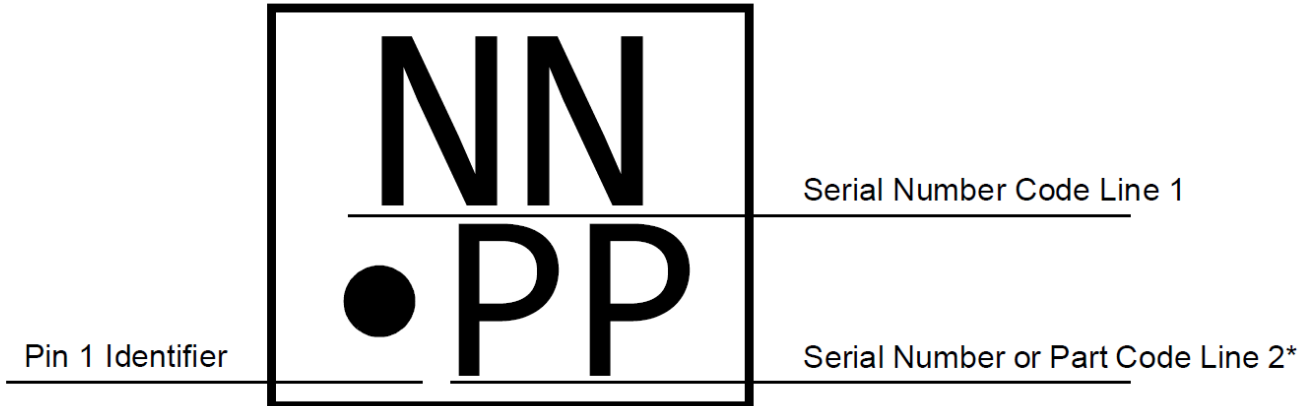
V _{OH}	HIGH-Level Output Voltage	Push-Pull 1X, Open Drain PMOS 1X, I _{OH} =100μA, at VDD=1.8V	1.692	1.788	--	V
		Push-Pull 1X, Open Drain PMOS 1X, I _{OH} =3mA, at VDD=3.3V	2.721	3.108	--	V
		Push-Pull 1X, Open Drain PMOS 1X, I _{OH} =5mA, at VDD=5.0V	4.171	4.761	--	V
V _{OL}	LOW-Level Output Voltage	Push-Pull 1X, I _{OL} =100μA, at VDD=1.8V	--	0.01	0.016	V
		Push-Pull 1X, I _{OL} =3mA, at VDD=3.3V	--	0.175	0.257	V
		Push-Pull 1X, I _{OL} =5mA, at VDD=5.0V	--	0.225	0.325	V
		Open Drain NMOS 2X, I _{OL} =100μA, at VDD=1.8V	--	0.003	0.003	V
		Open Drain NMOS 2X, I _{OL} =3mA, at VDD=3.3V	--	0.043	0.061	V
		Open Drain NMOS 2X, I _{OL} =5mA, at VDD=5.0V	--	0.057	0.08	V
I _{OH}	HIGH-Level Output Current (see Note 1)	Push-Pull 1X, Open Drain PMOS 1X, V _{OH} =VDD-0.2V, at VDD=1.8V	1.045	1.506	--	mA
		Push-Pull 1X, Open Drain PMOS 1X, V _{OH} =2.4V, at VDD=3.3V	5.774	11.066	--	mA
		Push-Pull 1X, Open Drain PMOS 1X, V _{OH} =2.4V, at VDD=5.0V	20.656	30.203	--	mA
I _{OL}	LOW-Level Output Current (see Note 1)	Push-Pull 1X, V _{OL} =0.15V, at VDD=1.8V	0.984	1.363	--	mA
		Push-Pull 1X, V _{OL} =0.4V, at VDD=3.3V	4.491	6.438	--	mA
		Push-Pull 1X, V _{OL} =0.4V, at VDD=5.0V	6.087	8.611	--	mA
		Open Drain NMOS 2X, V _{OL} =0.15V, at VDD=1.8V	4.02	5.471	--	mA
		Open Drain NMOS 2X, V _{OL} =0.4V, at VDD=3.3V	17.995	25.459	--	mA
		Open Drain NMOS 2X, V _{OL} =0.4V, at VDD=5.0V	24.032	33.581	--	mA
T _{SU}	Startup Time	From VDD rising past P _{ON} _{THR}	--	0.54	--	ms
P _{ON} _{THR}	Power On Threshold	V _{DD} Level Required to Start Up the Chip	1.303	1.506	1.707	V
P _{OFF} _{THR}	Power Off Threshold	V _{DD} Level Required to Switch Off the Chip	0.675	0.901	1.174	V

Note:

- DC or average current through any pin should not exceed value given in Absolute Maximum Conditions.
- The GreenPAK's power rails are divided in two sides. Pins 2, 3 and 4 are connected to one side, pins 6, 7 and 8 to another.

3. Guaranteed by Design.

Package Top Marking



* PP may consist of the special characters +, -, and = for a total of 9 different combinations, or may consist of two character alphanumeric Part Code (A-Z and 0-9), depending on time of marking.

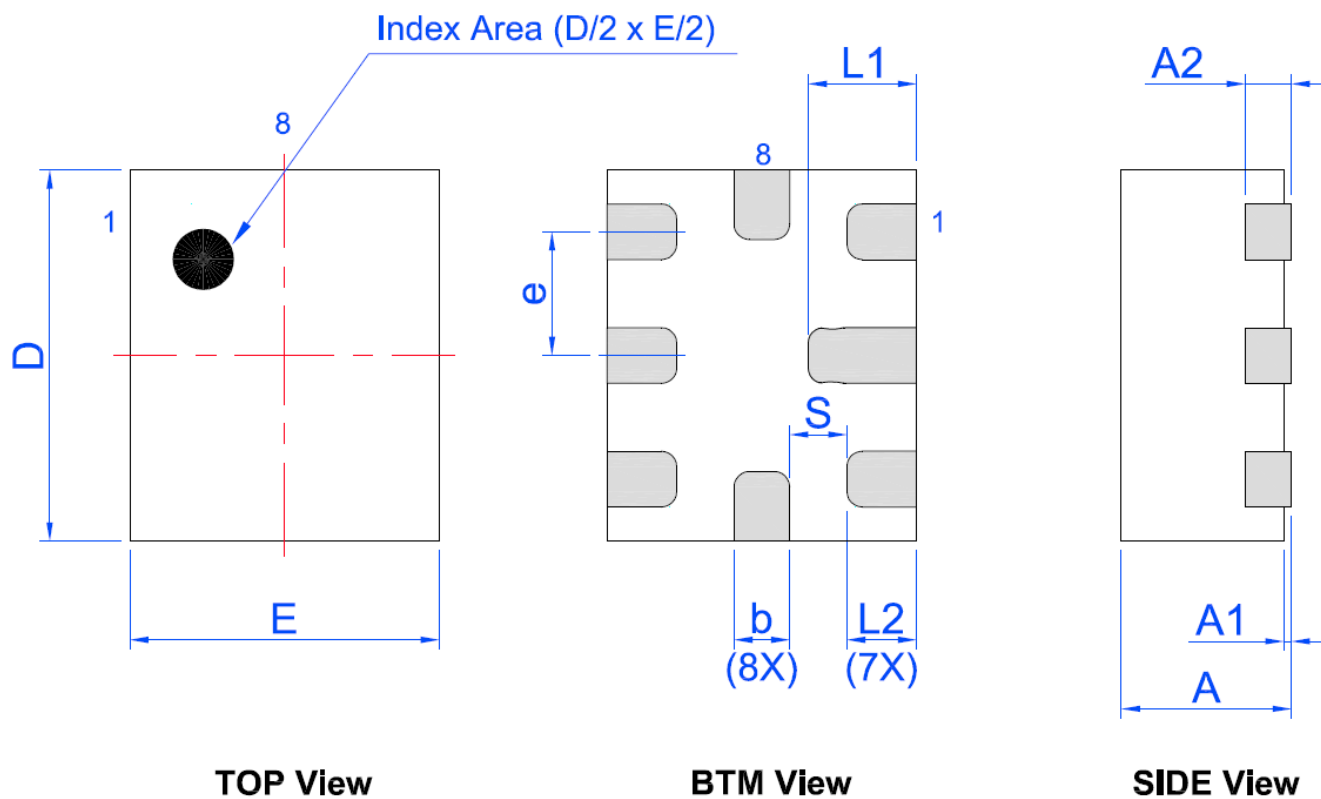
Note: The SN Code (Line 1 and Line 2) is generated during production, and encodes information including part number, programming code number, date code and lot code. This same information is provided in plain text form on a label placed on the reel. If you need assistance in decoding the SN Code, please contact Dialog Semiconductor.

Datasheet Revision	Programming Code Number	Lock Status	Checksum	Part Code	Revision	Date
0.10	001	U	0xC19D7C8B			04/04/2023

The IC security bit is locked/set for code security for production unless otherwise specified. The Programming Code Number is not changed based on the choice of locked vs. unlocked status.

Package Drawing and Dimensions

8 Lead STQFN Package 1.0 x 1.2 mm



Unit: mm

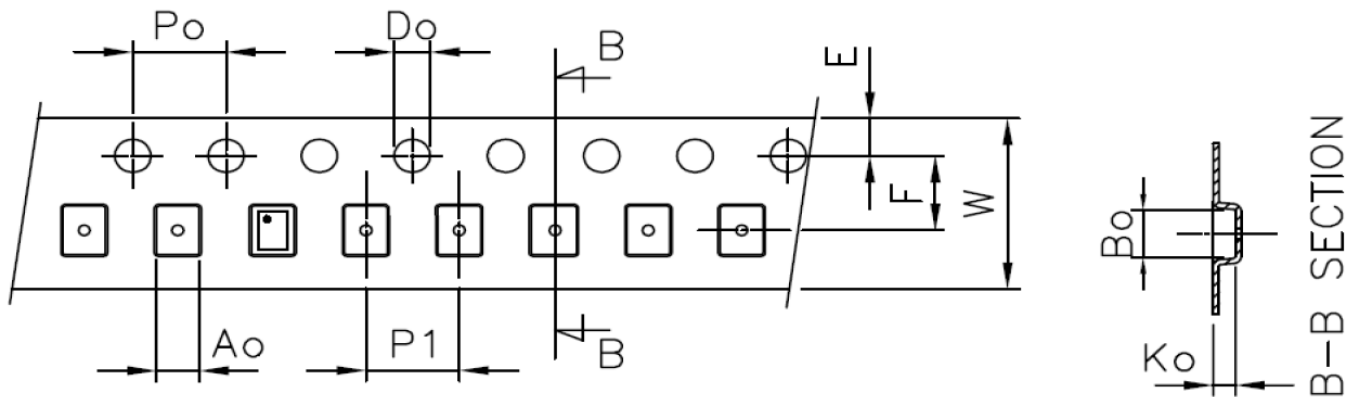
Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max
A	0.50	0.55	0.60	D	1.15	1.20	1.25
A1	0.005	-	0.050	E	0.95	1.00	1.05
A2	0.10	0.15	0.20	L1	0.30	0.35	0.40
b	0.13	0.18	0.23	L2	0.175	0.225	0.275
e	0.40 BSC			S	0.185 REF		

Tape and Reel Specification

Package Type	# of Pins	Nominal Package Size [mm]	Max Units		Reel & Hub Size [mm]	Leader (min)		Trailer (min)		Tape Width [mm]	Part Pitch [mm]
			per Reel	per Box		Pockets	Length [mm]	Pockets	Length [mm]		
STQFN 8L 0.4P FC Green	8	1.0x1.2x0.55	3000	3000	178/60	100	400	100	400	8	4

Carrier Tape Drawing and Dimensions

Package Type	Pocket BTM Length	Pocket BTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge	Index Hole to Pocket Center	Tape Width
	A0	B0	K0	P0	P1	D0	E	F	
STQFN 8L 0.4P FC Green	1.16	1.38	0.71	4	4	1.5	1.75	3.5	8



Recommended Reflow Soldering Profile

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 0.66 mm³ (nominal). More information can be found at www.jedec.org.

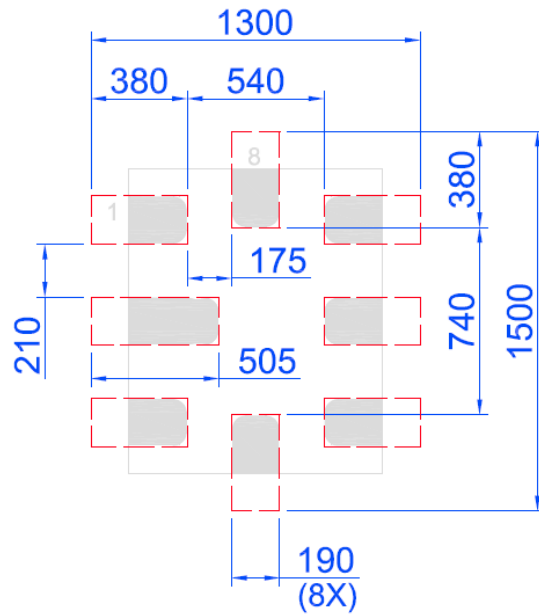
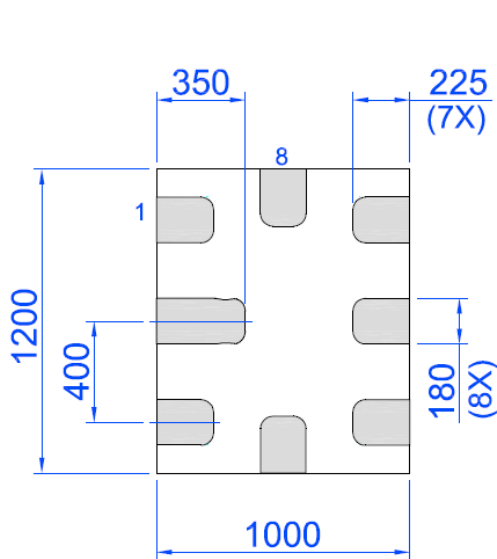
Recommended Land Pattern



**Exposed Pad
(PKG face down)**



**Recommended Landing Pattern
(PKG face down)**



Unit: um

Datasheet Revision History

Date	Version	Change
04/04/2023	0.10	New design for SLG46108 chip

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